74HC423; 74HCT423

Dual retriggerable monostable multivibrator with reset

Rev. 03 — 24 July 2008 Product data sheet

1. General description

74HC423; 74HCT423 are high-speed Si-gate CMOS devices that are pin compatible with low power Schottky TTL (LSTTL). They are specified in compliance with JEDEC standard no. 7A.

The 74HC423; 74HCT423 dual retriggerable monostable multivibrator with reset has two methods of output pulse width control.

1. The minimum pulse width is essentially determined by the selection of an external resistor (R_{EXT}) and capacitor (C_{EXT}), see Section 12.1.
2. Once triggered, the basic output pulse width may be extended by retriggering the gated active LOW-going edge input ($n\overline{A}$) or the active HIGH-going edge input (nB). By repeating this process, the output pulse period (nQ = HIGH, $n\overline{Q}$ = LOW) can be made as long as desired. When $n\overline{R}D$ is LOW, it forces the nQ output LOW, the $n\overline{Q}$ output HIGH and also inhibits the triggering. Figure 10 and Figure 11 illustrate pulse control by reset.

The $n\overline{A}$ and nB inputs' Schmitt trigger action makes them highly tolerant to slower input rise and fall times.

The 74HC423; 74HCT423 are identical to the 74HC123; 74HCT123 except that they cannot be triggered via the reset input.

2. Features

- DC triggered from active HIGH or active LOW inputs
- Retriggerable for very long pulses up to 100% duty factor
- Direct reset terminates output pulse
- Schmitt-trigger action on all inputs except for the reset input
- Complies with JEDEC standard no. 7A
- ESD protection:
  - HBM JESD22-A114E exceeds 2000 V
  - MM JESD22-A115-A exceeds 200 V
- Specified from –40 °C to +85 °C and from –40 °C to +125 °C

3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74HC423N	–40 °C to +125 °C	DIP16	plastic dual in-line package; 16 leads (300 mil)	SOT38-4
74HCT423N				
74HC423D	–40 °C to +125 °C	SO16	plastic small outline package; 16 leads; body width 3.9 mm	SOT109-1
74HCT423D				
74HC423BQ	–40 °C to +125 °C	DHVQFN16	plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 16 terminals; body 2.5 × 3.5 × 0.85 mm	SOT763-1
74HCT423BQ				
74HCT423DB	–40 °C to +125 °C	SSOP16	plastic shrink small outline package; 16 leads; body width 5.3 mm	SOT338-1
74HCT423PW	–40 °C to +125 °C	TSSOP16	plastic thin shrink small outline package; 16 leads; body width 4.4 mm	SOT403-1

4. Functional diagram

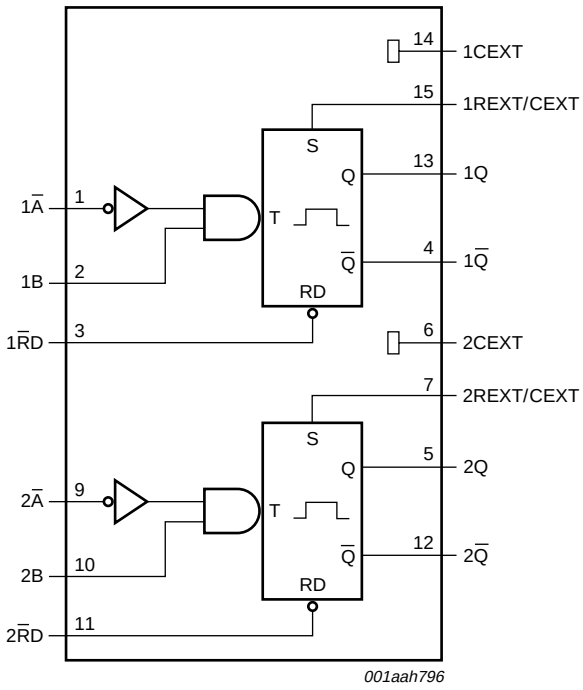


Fig 1. Functional Diagram

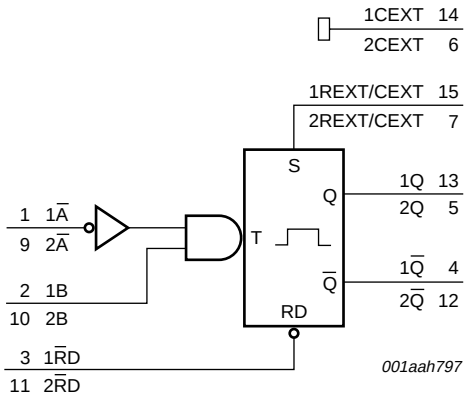


Fig 2. Logic symbol

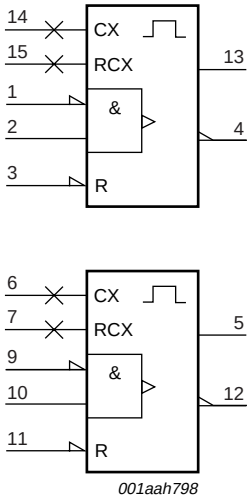


Fig 3. IEC Logic symbol

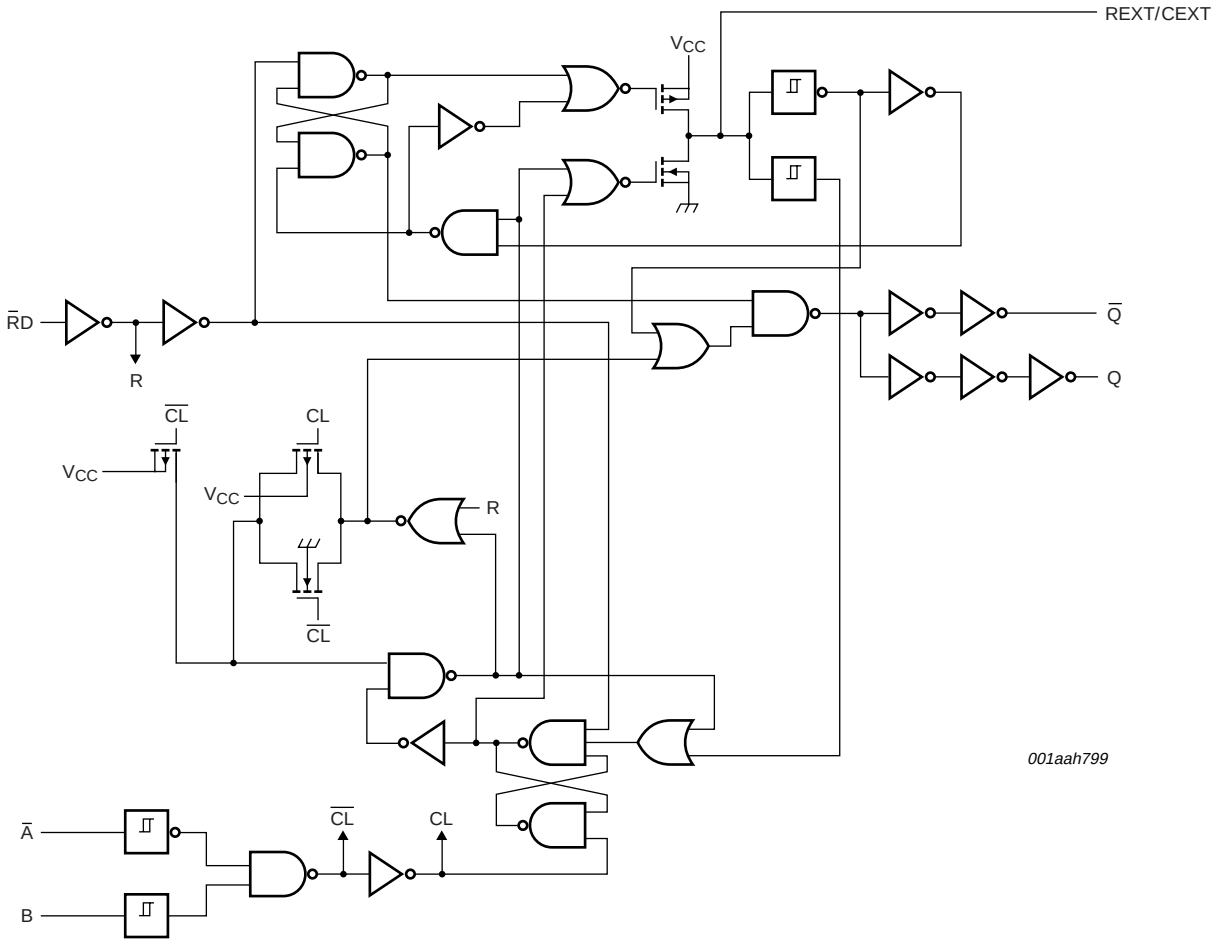


Fig 4. Logic diagram

5. Pinning information

5.1 Pinning

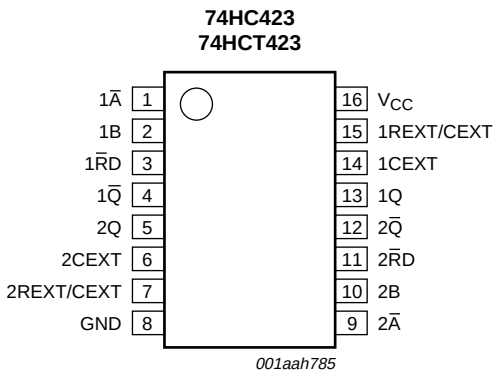
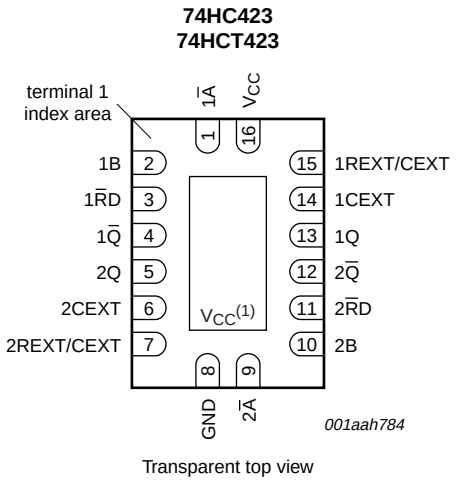


Fig 5. Pin configuration DIP16, SO16 and (T)SSOP16



Transparent top view

(1) The die substrate is attached to this pad using a conductive die attach material. It cannot be used as supply pin or input

Fig 6. Pin configuration DHVQFN16

5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
1Ā, 2Ā	1, 9	trigger input (negative edge triggered)
1B, 2B	2, 10	trigger input (positive edge triggered)
1R̄D, 2R̄D	3, 11	direct reset (active LOW)
1Q̄, 2Q̄	4, 12	output (active LOW)
GND	8	ground (0 V)
1Q, 2Q	13, 5	output (active HIGH)
1CEXT, 2CEXT	14, 6	external capacitor connection
1REXT/CEXT, 2REXT/CEXT	15, 7	external resistor/capacitor connection
V_{CC}	16	supply voltage

6. Functional description

Table 3. Function table[1]

Input			Output	
$n\overline{RD}$	$n\overline{A}$	nB	nQ	$n\overline{Q}$
L	X	X	L	H
X	H	X	L[2]	H[2]
X	X	L	L[2]	H[2]
H	L	↑	⊓	⊔
H	↓	H	⊓	⊔

[1] H = HIGH voltage level;
L = LOW voltage level;
X = don't care;
↑ = LOW-to-HIGH transition;
↓ = HIGH-to-LOW transition;
⊓ = one HIGH level output pulse;
⊔ = one LOW level output pulse.

[2] If the monostable multivibrator was triggered before this condition was established, the pulse will continue as programmed.

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CC}	supply voltage			–0.5	+7	V
I_{IK}	input clamping current	$V_I < -0.5$ V or $V_I > V_{CC} + 0.5$ V	[1]	-	±20	mA
I_{OK}	output clamping current	$V_O < -0.5$ V or $V_O > V_{CC} + 0.5$ V	[1]	-	±20	mA
I_O	output current	-0.5 V $< V_O < V_{CC} + 0.5$ V		-	±25	mA
I_{CC}	supply current			-	50	mA
I_{GND}	ground current			–50	-	mA
T_{stg}	storage temperature			–65	+150	°C
P_{tot}	total power dissipation	DIP16 package	[2]	-	750	mW
		SO16, SSOP16, TSSOP16 and DHVQFN16 packages	[3]	-	500	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For DIP16 packages: above 70 °C the value of P_{tot} derates linearly at 12 mW/K.

[3] For SO16 packages: above 70 °C the value of P_{tot} derates linearly at 8 mW/K;
For SSOP16 and TSSOP16 packages: above 60 °C the value of P_{tot} derates linearly at 5.5 mW/K;
For DHVQFN16 packages: above 60 °C the value of P_{tot} derates linearly at 4.5 mW/K.

8. Recommended operating conditions

Table 5. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	74HC423			74HCT423			Unit
			Min	Typ	Max	Min	Typ	Max	
V_{CC}	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
V_I	input voltage		0	-	V_{CC}	0	-	V_{CC}	V
V_O	output voltage		0	-	V_{CC}	0	-	V_{CC}	V
T_{amb}	ambient temperature		–40	-	+125	–40	-	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	V_{CC} = 2.0 V	-	-	625	-	-	-	ns/V
		V_{CC} = 4.5 V	-	1.67	139	-	1.67	139	ns/V
		V_{CC} = 6.0 V	-	-	83	-	-	-	ns/V

9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
74HC423										
V_{IH}	HIGH-level input voltage	V_{CC} = 2.0 V	1.5	1.2	-	1.5	-	1.5	-	V
		V_{CC} = 4.5 V	3.15	2.4	-	3.15	-	3.15	-	V
		V_{CC} = 6.0 V	4.2	3.2	-	4.2	-	4.2	-	V
V_{IL}	LOW-level input voltage	V_{CC} = 2.0 V	-	0.8	0.5	-	0.5	-	0.5	V
		V_{CC} = 4.5 V	-	2.1	1.35	-	1.35	-	1.35	V
		V_{CC} = 6.0 V	-	2.8	1.8	-	1.8	-	1.8	V
V_{OH}	HIGH-level output voltage	V_I = V_{IH} or V_{IL}								
		I_O = –20 µA; V_{CC} = 2.0 V	1.9	2.0	-	1.9	-	1.9	-	V
		I_O = –20 µA; V_{CC} = 4.5 V	4.4	4.5	-	4.4	-	4.4	-	V
		I_O = –20 µA; V_{CC} = 6.0 V	5.9	6.0	-	5.9	-	5.9	-	V
		I_O = –4.0 mA; V_{CC} = 4.5 V	3.98	4.32	-	3.84	-	3.7	-	V
		I_O = –5.2 mA; V_{CC} = 6.0 V	5.48	5.81	-	5.34	-	5.2	-	V
V_{OL}	LOW-level output voltage	V_I = V_{IH} or V_{IL}								
		I_O = 20 µA; V_{CC} = 2.0 V	-	0	0.1	-	0.1	-	0.1	V
		I_O = 20 µA; V_{CC} = 4.5 V	-	0	0.1	-	0.1	-	0.1	V
		I_O = 20 µA; V_{CC} = 6.0 V	-	0	0.1	-	0.1	-	0.1	V
		I_O = 4.0 mA; V_{CC} = 4.5 V	-	0.15	0.26	-	0.33	-	0.4	V
		I_O = 5.2 mA; V_{CC} = 6.0 V	-	0.16	0.26	-	0.33	-	0.4	V
I_I	input leakage current	V_I = V_{CC} or GND; V_{CC} = 6.0 V	-	-	±0.1	-	±1.0	-	±1.0	µA
I_{CC}	supply current	V_I = V_{CC} or GND; I_O = 0 A; V_{CC} = 6.0 V	-	-	8.0	-	80	-	160	µA

Table 6. Static characteristics *…continued*

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
C_I	input capacitance		-	3.5	-	-	-	-	-	pF
74HCT423										
V_{IH}	HIGH-level input voltage	V_{CC} = 4.5 V to 5.5 V	2.0	1.6	-	2.0	-	2.0	-	V
V_{IL}	LOW-level input voltage	V_{CC} = 4.5 V to 5.5 V	-	1.2	0.8	-	0.8	-	0.8	V
V_{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}; V_{CC} = 4.5 V								
		I_O = –20 µA	4.4	4.5	-	4.4	-	4.4	-	V
		I_O = –4.0 mA	3.98	4.32	-	3.84	-	3.7	-	V
V_{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}; V_{CC} = 4.5 V								
		I_O = 20 µA	-	0	0.1	-	0.1	-	0.1	V
		I_O = 4.0 mA	-	0.15	0.26	-	0.33	-	0.4	V
I_I	input leakage current	$V_I = V_{CC}$ or GND; V_{CC} = 5.5 V	-	-	±0.1	-	±1.0	-	±1.0	µA
I_{CC}	supply current	$V_I = V_{CC}$ or GND; V_{CC} = 5.5 V; I_O = 0 A	-	-	8.0	-	80	-	160	µA
ΔI_{CC}	additional supply current	per input pin; $V_I = V_{CC}$ – 2.1 V; other inputs at V_{CC} or GND; V_{CC} = 4.5 V to 5.5 V; I_O = 0 A								
		$n\overline{A}$, nB inputs	-	35	126	-	158	-	172	µA
		$n\overline{R}D$ input	-	50	180	-	225	-	245	µA
C_I	input capacitance		-	3.5	-	-	-	-	-	pF

10. Dynamic characteristics

Table 7. Dynamic characteristics

GND = 0 V; test circuit see Figure 12.

Symbol	Parameter	Conditions		25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
				Min	Typ	Max	Min	Max	Min	Max	
74HC423											
t_{pd}	propagation delay	$n\overline{A}$ or nB to nQ or $n\overline{Q}$; R_{EXT} = 5 kΩ; C_{EXT} = 0 pF; see Figure 7	[1]								
		V_{CC} = 2.0 V		-	80	255	-	320	-	385	ns
		V_{CC} = 4.5 V		-	29	51	-	64	-	77	ns
		V_{CC} = 5.0 V; C_L = 15 pF		-	25	-	-	-	-	-	ns
		V_{CC} = 6.0 V		-	23	43	-	54	-	65	ns
		$n\overline{R}D$ to nQ or $n\overline{Q}$; see Figure 7	[1]								
		V_{CC} = 2.0 V		-	66	215	-	270	-	325	ns
		V_{CC} = 4.5 V		-	24	43	-	54	-	65	ns
		V_{CC} = 5.0 V; C_L = 15 pF		-	20	-	-	-	-	-	ns
		V_{CC} = 6.0 V		-	19	37	-	46	-	55	ns
t_t	transition time	see Figure 7	[2]								
		V_{CC} = 2.0 V		-	19	75	-	95	-	110	ns
		V_{CC} = 4.5 V		-	7	15	-	19	-	22	ns
		V_{CC} = 6.0 V		-	6	13	-	16	-	19	ns
t_W	pulse width	$n\overline{A}$ input LOW; see Figure 7 and Figure 8									
		V_{CC} = 2.0 V		100	11	-	125	-	150	-	ns
		V_{CC} = 4.5 V		20	4	-	25	-	30	-	ns
		V_{CC} = 6.0 V		17	3	-	21	-	26	-	ns
		nB input HIGH; see Figure 7 and Figure 8									
		V_{CC} = 2.0 V		100	17	-	125	-	150	-	ns
		V_{CC} = 4.5 V		20	6	-	25	-	30	-	ns
		V_{CC} = 6.0 V		17	5	-	21	-	26	-	ns
		$n\overline{R}D$ input LOW; see Figure 7 and Figure 8									
		V_{CC} = 2.0 V		100	14	-	125	-	150	-	ns
		V_{CC} = 4.5 V		20	5	-	25	-	30	-	ns
		V_{CC} = 6.0 V		17	4	-	21	-	26	-	ns
		nQ HIGH or $n\overline{Q}$ LOW; V_{CC} = 5.0 V; R_{EXT} = 10 kΩ; C_{EXT} = 100 nF; see Figure 7 and Figure 8		-	450	-	-	-	-	-	µs
		nQ HIGH or $n\overline{Q}$ LOW; V_{CC} = 5.0 V; R_{EXT} = 5 kΩ; C_{EXT} = 0 pF; V_I = GND to V_{CC}; see Figure 7 and Figure 8	[3]	-	75	-	-	-	-	-	ns
t_{rtrig}	retrigger time	$n\overline{A}$ or nB input; V_{CC} = 5.0 V; R_{EXT} = 5 kΩ; C_{EXT} = 0 pF; see Figure 10	[4]	-	110	-	-	-	-	-	ns

Table 7. Dynamic characteristics *…continued*

GND = 0 V; test circuit see Figure 12.

Symbol	Parameter	Conditions		25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
				Min	Typ	Max	Min	Max	Min	Max	
R_{EXT}	external timing resistor	V_{CC} = 2.0 V; see Figure 8		10	-	1000	-	-	-	-	kΩ
		V_{CC} = 5.0 V		2	-	1000	-	-	-	-	kΩ
C_{EXT}	external timing capacitor	V_{CC} = 5.0 V; see Figure 8	[5]			no limits					pF
C_{PD}	power dissipation capacitance	per package; V_I = GND to V_{CC}	[6]	-	54	-	-	-	-	-	pF
74HCT423											
t_{pd}	propagation delay	$n\overline{A}$ or nB to nQ or $n\overline{Q}$; R_{EXT} = 5 kΩ; C_{EXT} = 0 pF; see Figure 7									
		V_{CC} = 4.5 V	[1]	-	30	51	-	64	-	77	ns
		V_{CC} = 5.0 V; C_L = 15 pF	[1]	-	26	-	-	-	-	-	ns
		$n\overline{R}D$ to nQ or $n\overline{Q}$; R_{EXT} = 5 kΩ; C_{EXT} = 0 pF; see Figure 7	[1]	-	26	48	-	60	-	72	ns
		V_{CC} = 4.5 V	[1]	-	26	48	-	60	-	72	ns
		V_{CC} = 5.0 V; C_L = 15 pF	[1]	-	22	-	-	-	-	-	ns
t_t	transition time	V_{CC} = 4.5 V; Figure 7	[2]	-	7	15	-	19	-	22	ns
t_W	pulse width	trigger pulse; $n\overline{A}$ input LOW; V_{CC} = 4.5 V; see Figure 7 and Figure 10		20	5	-	25	-	30	-	ns
		trigger pulse; nB input HIGH; V_{CC} = 4.5 V; see Figure 7 and Figure 10		20	5	-	25	-	30	-	ns
		reset pulse; $n\overline{R}D$ input LOW; V_{CC} = 4.5 V; see Figure 7 and Figure 11		20	7	-	25	-	30	-	ns
		output pulse; nQ HIGH or $n\overline{Q}$ LOW; V_{CC} = 5.0 V; R_{EXT} = 10 kΩ; C_{EXT} = 100 nF; see Figure 7, Figure 10 and Figure 11		-	450	-	-	-	-	-	µs
		output pulse; nQ HIGH or $n\overline{Q}$ LOW; V_{CC} = 5.0 V; R_{EXT} = 5 kΩ; C_{EXT} = 0 pF; V_I = GND to V_{CC} – 1.5 V; see Figure 7, Figure 10 and Figure 11	[3]	-	75	-	-	-	-	-	ns
t_{rtrig}	retrigger time	$n\overline{A}$ or nB input; V_{CC} = 5.0 V; R_{EXT} = 5 kΩ; C_{EXT} = 0 pF; see Figure 10		-	110	-	-	-	-	-	ns
R_{EXT}	external timing resistor	V_{CC} = 5.0 V; see Figure 8		2	-	1000	-	-	-	-	kΩ
C_{EXT}	external timing capacitor	V_{CC} = 5.0 V; see Figure 8	[5]			no limits					pF

Table 7. Dynamic characteristics *…continued*

GND = 0 V; test circuit see Figure 12.

Symbol	Parameter	Conditions		25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
				Min	Typ	Max	Min	Max	Min	Max	
C_{PD}	power dissipation capacitance	per package; V_I = GND to V_{CC} – 1.5 V	[6]	-	56	-	-	-	-	-	pF

[1] t_{pd} is the same as t_{PHL} and t_{PLH}.

[2] t_t is the same as t_{THL} and t_{TLH}.

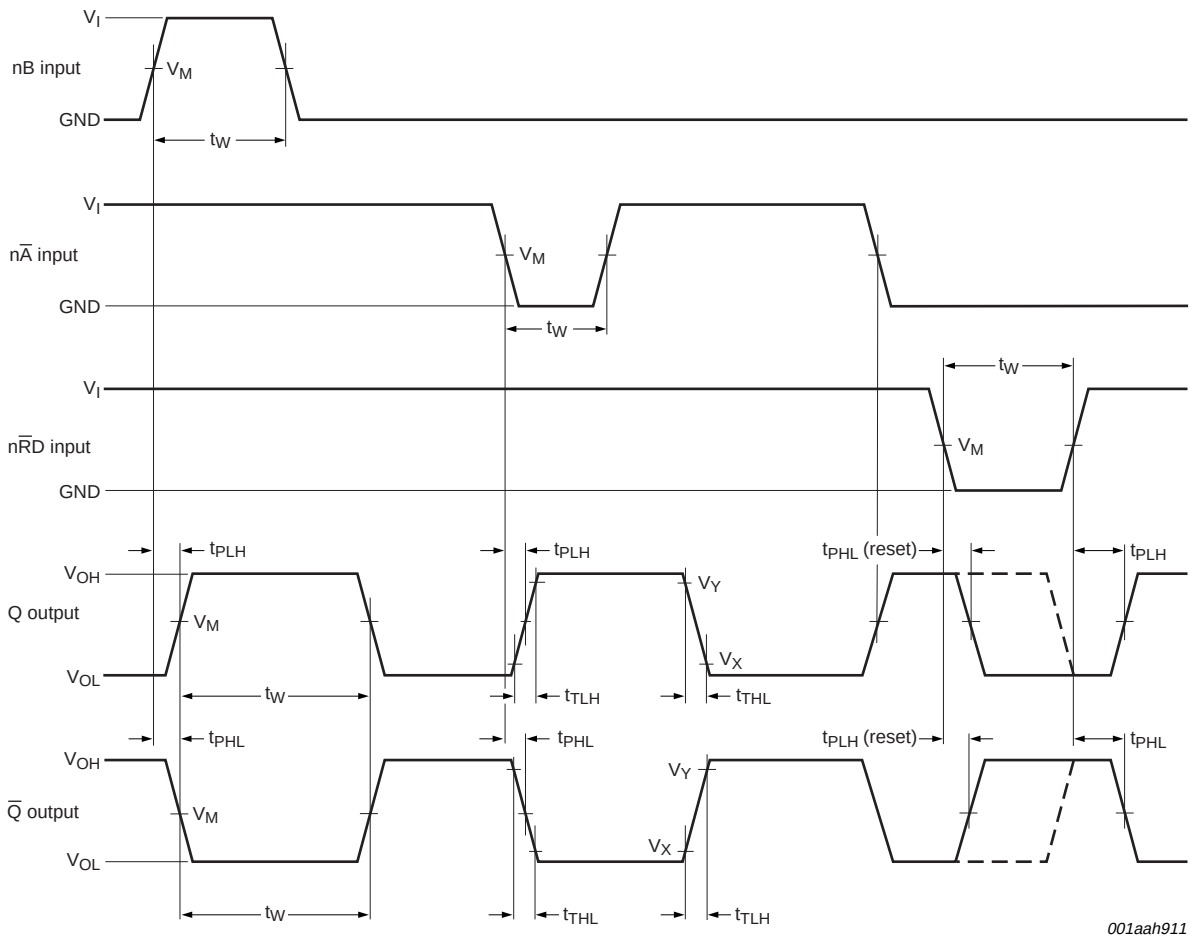
[3] For other R_{EXT} and C_{EXT} combinations see Figure 8. If C_{EXT} > 10 pF, the next formula is valid:
$t_W = K \times R_{EXT} \times C_{EXT}$ (typ.), where:
t_W = output pulse width in ns;
R_{EXT} = external resistor in kΩ;
C_{EXT} = external capacitor in pF;
K = 0.55 for V_{CC} = 2.0 V and 0.45 for V_{CC} = 5.0 V; see Figure 9.
Inherent test jig and pin capacitance at pins 15 and 7 (nREXT/CEXT) is 7 pF.

[4] The time to retrigger the monostable multivibrator depends on the values of R_{EXT} and C_{EXT}. The output pulse width will only be extended when the time between the active-going edges of the trigger input pulses meets the minimum retrigger time.
If C_{EXT} > 10 pF, the next formula (at V_{CC} = 5.0 V) for the set-up time of a retrigger pulse is valid:
$t_{rtrig} = 30 + 0.19 \times R_{EXT} \times C_{EXT}^{0.9} + 13 \times R_{EXT}^{1.05}$ (typ.); where:
t_{rtrig} = retrigger time in ns;
C_{EXT} = external capacitor in pF;
R_{EXT} = external resistor in kΩ.
Inherent test jig and pin capacitance at pins 15 and 7 (nREXT/CEXT) is 7 pF.

[5] When the device is powered-up, initiate the device via a reset pulse, when C_{EXT} < 50 pF.

[6] C_{PD} is used to determine the dynamic power dissipation (P_D in µW):
$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \sum (C_L \times V_{CC}^2 \times f_o)$; where:
f_i = input frequency in MHz;
f_o = output frequency in MHz;
C_L = output load capacitance in pF;
V_{CC} = supply voltage in V;
N = number of inputs switching;
$\sum (C_L \times V_{CC}^2 \times f_o)$ = sum of outputs.

11. Waveforms



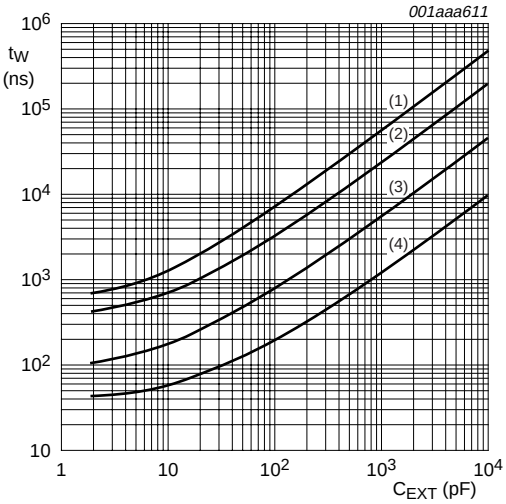
Measurement points are given in Table 8.

V_{OL} and V_{OH} are typical voltage output levels that occur with the output load.

Fig 7. Pulse widths, propagation delays from inputs (nA, nB, nRD) to outputs (nQ, nQ) and output transition times

Table 8. Measurement points

Type	Input		Output		
	V_I	V_M	V_M	V_X	V_Y
74HC423	V_{CC}	$0.5V_{CC}$	$0.5V_{CC}$	$0.1V_{CC}$	$0.9V_{CC}$
74HCT423	3 V	1.3 V	1.3 V	$0.1V_{CC}$	$0.9V_{CC}$



V_{CC} = 5.0 V and T_{amb} = 25 °C.

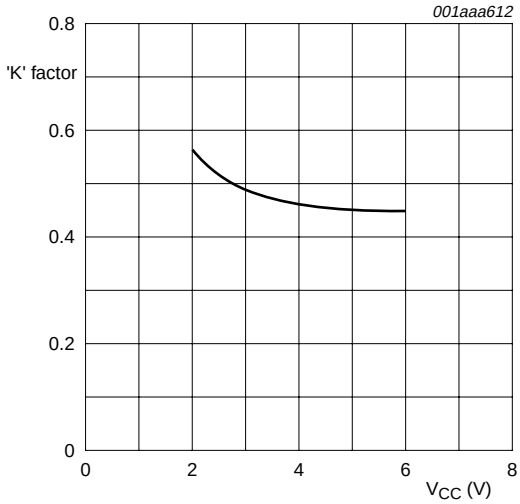
(1) R_{EXT} = 100 kΩ.

(2) R_{EXT} = 50 kΩ.

(3) R_{EXT} = 10 kΩ.

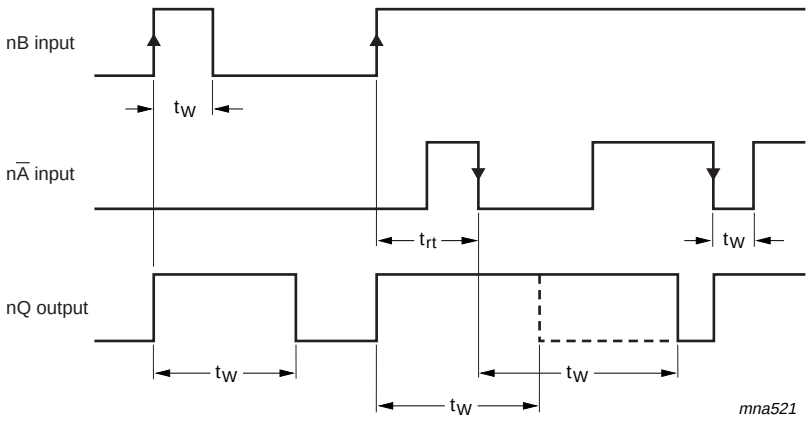
(4) R_{EXT} = 2 kΩ.

Fig 8. Typical output pulse width as a function of the external capacitor values



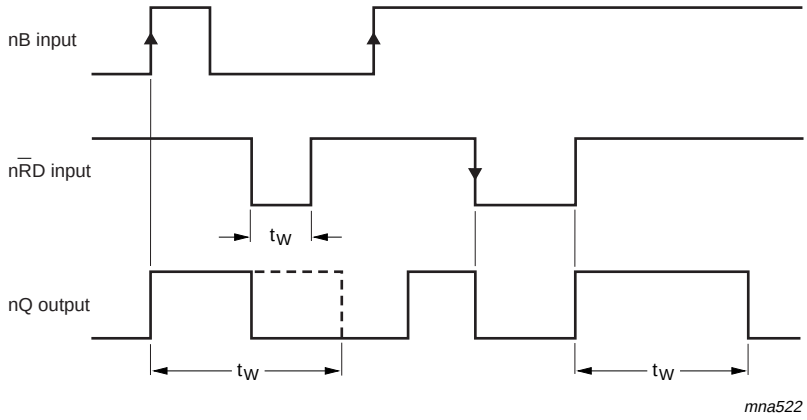
External capacitance = 10 nF,
external resistance = 10 kΩ to 100 kΩ and T_{amb} = 25 °C.

Fig 9. Typical 'K' factor



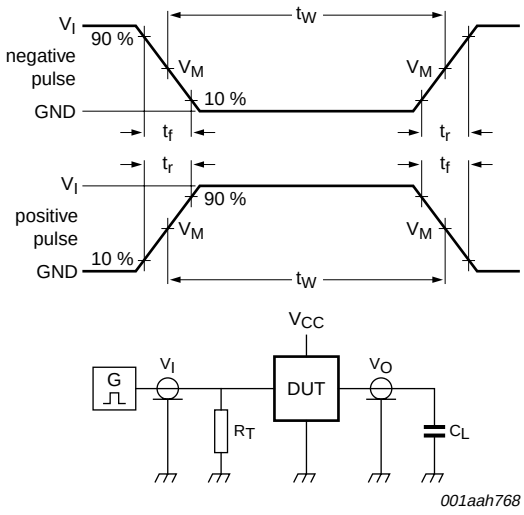
nR̅D = HIGH.

Fig 10. Output pulse control using retrigger pulse (t_{rtrig})



nA = LOW.

Fig 11. Output pulse control using reset input nRD



Test data is given in Table 9.

Definitions for test circuit:

R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator.

C_L = Load capacitance including jig and probe capacitance.

Fig 12. Test circuit for measuring switching times

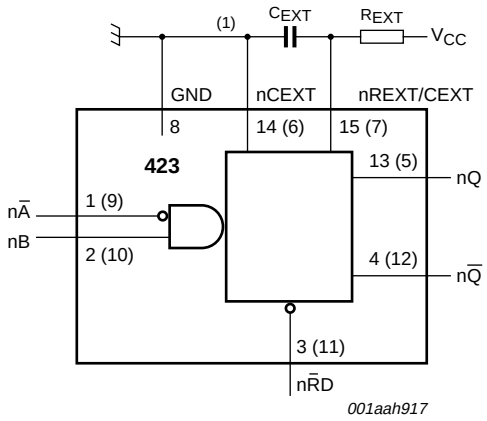
Table 9. Test data

Supply	Input		Load
V_{CC}	V_I	t_r, t_f	C_L
2.0 V to 6.0 V	V_{CC}	6 ns	15 pF, 50 pF

12. Application information

12.1 Timing component connections

The basic output pulse width is essentially determined by the values of the external timing components R_{EXT} and C_{EXT}.



(1) For minimum noise generation it is recommended that the nCEXT pins (6, 14) are connected to ground externally to the GND pin (8).

Fig 13. Timing component connections

12.1.1 Minimum monostable pulse width

To set the minimum pulse width, when C_{EXT} < 10 nF, see Figure 8 and when C_{EXT} > 10 nF, the output pulse width is defined as:

$t_W = 0.45 \times R_{EXT} \times C_{EXT}$ (typ.), where:

t_W = pulse width in µs;

R_{EXT} = external resistor in kΩ;

C_{EXT} = external capacitor in nF.

12.2 Power-up considerations

When the monostable is powered-up it may produce an output pulse, with a pulse width defined by the values of R_{EXT} and C_{EXT}, this output pulse can be eliminated using the circuit shown in Figure 14.

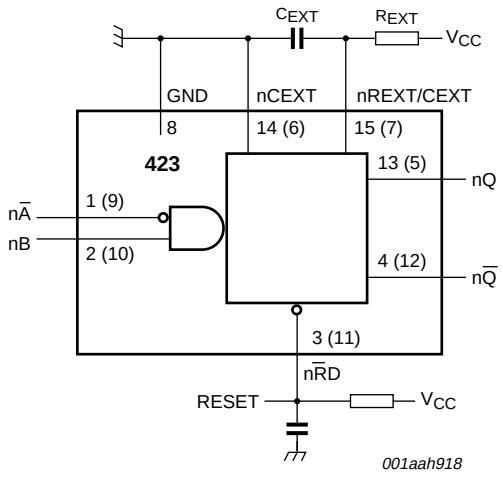


Fig 14. Power-up output pulse elimination circuit

12.3 Power-down considerations

A large capacitor C_{EXT} may cause problems when powering-down the monostable due to the capacitor's stored energy. When a system containing this device is powered-down or a rapid decrease of V_{CC} to zero occurs, the monostable may sustain damage, due to the capacitor discharging through the input protection diodes. To avoid this possibility, use a damping diode D_{EXT} preferably a germanium or Schottky type diode able to withstand large current surges and connect as shown in Figure 15.

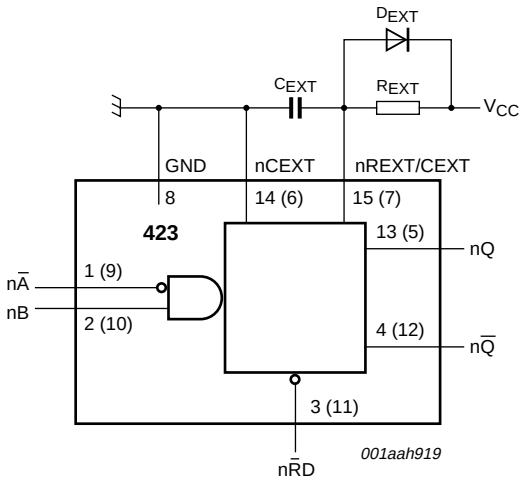
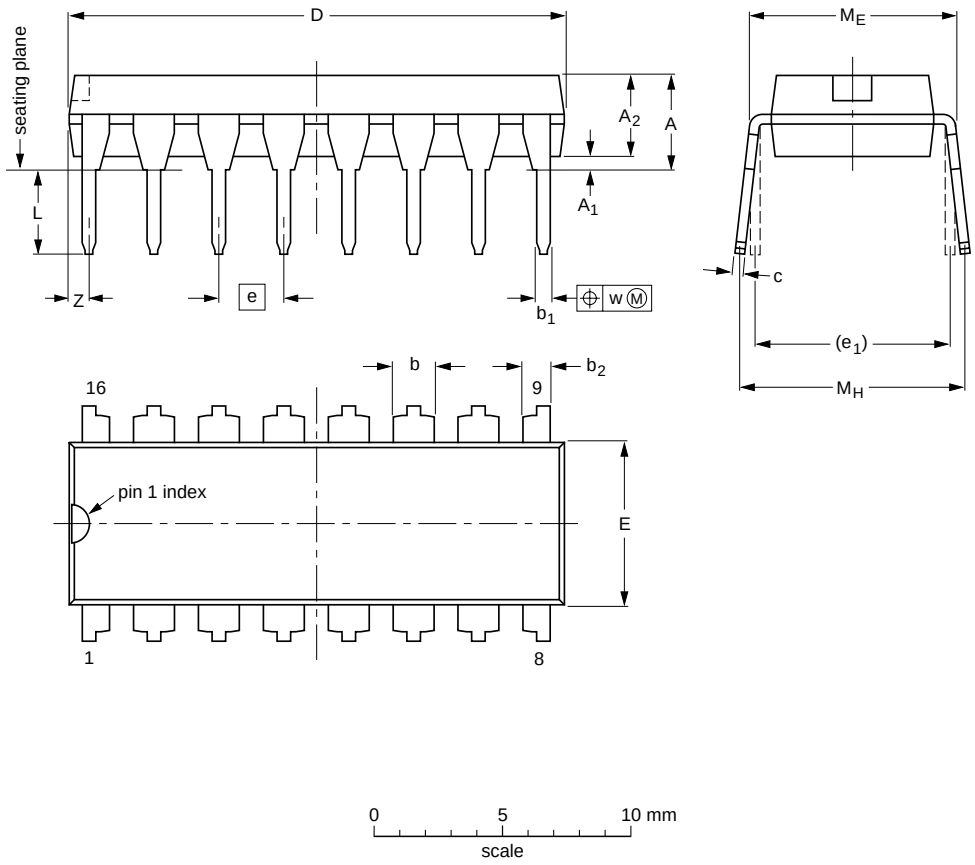


Fig 15. Power-down protection circuit

13. Package outline

DIP16: plastic dual in-line package; 16 leads (300 mil) **SOT38-4**



DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A_1 min.	A_2 max.	b	b_1	b_2	c	D (1)	E (1)	e	e_1	L	M_E	M_H	w	Z (1) max.
mm	4.2	0.51	3.2	1.73 1.30	0.53 0.38	1.25 0.85	0.36 0.23	19.50 18.55	6.48 6.20	2.54	7.62	3.60 3.05	8.25 7.80	10.0 8.3	0.254	0.76
inches	0.17	0.02	0.13	0.068 0.051	0.021 0.015	0.049 0.033	0.014 0.009	0.77 0.73	0.26 0.24	0.1	0.3	0.14 0.12	0.32 0.31	0.39 0.33	0.01	0.03

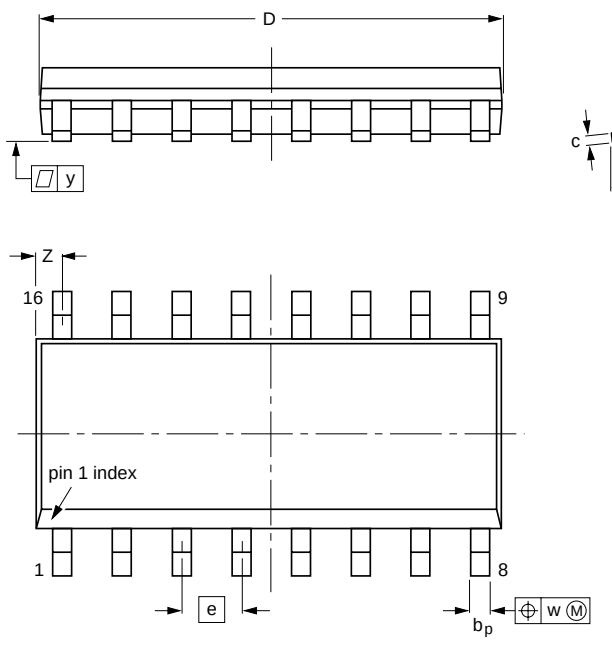
Note

1. Plastic or metal protrusions of 0.25 mm (0.01 inch) maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT38-4						~~95-01-14~~ 03-02-13

Fig 16. Package outline SOT38-4 (DIP16)

SO16: plastic small outline package; 16 leads; body width 3.9 mm **SOT109-1**



DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	$D^{(1)}$	$E^{(1)}$	e	H_E	L	L_p	Q	v	w	y	$Z^{(1)}$	θ
mm	1.75	0.25 0.10	1.45 1.25	0.25	0.49 0.36	0.25 0.19	10.0 9.8	4.0 3.8	1.27	6.2 5.8	1.05	1.0 0.4	0.7 0.6	0.25	0.25	0.1	0.7 0.3	8^o 0^o
inches	0.069	0.010 0.004	0.057 0.049	0.01	0.019 0.014	0.0100 0.0075	0.39 0.38	0.16 0.15	0.05	0.244 0.228	0.041	0.039 0.016	0.028 0.020	0.01	0.01	0.004	0.028 0.012	

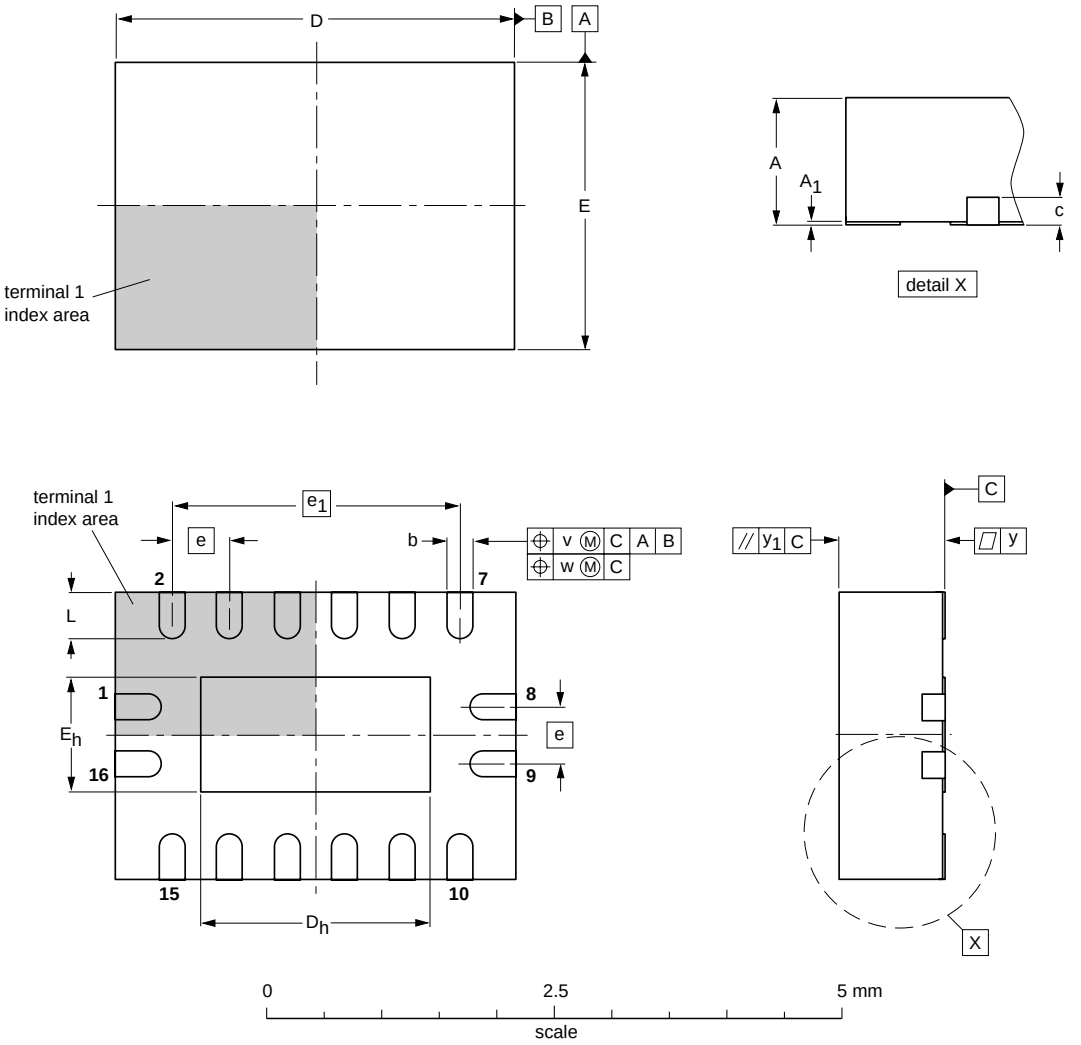
Note

1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT109-1	076E07	MS-012				~~99-12-27~~ 03-02-19

Fig 17. Package outline SOT109-1 (SO16)

DHVQFN16: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 16 terminals; body 2.5 x 3.5 x 0.85 mm **SOT763-1**



DIMENSIONS (mm are the original dimensions)

UNIT	A(1) max.	A_1	b	c	D(1)	D_h	E(1)	E_h	e	e_1	L	v	w	y	y_1
mm	1	0.05 0.00	0.30 0.18	0.2	3.6 3.4	2.15 1.85	2.6 2.4	1.15 0.85	0.5	2.5	0.5 0.3	0.1	0.05	0.05	0.1

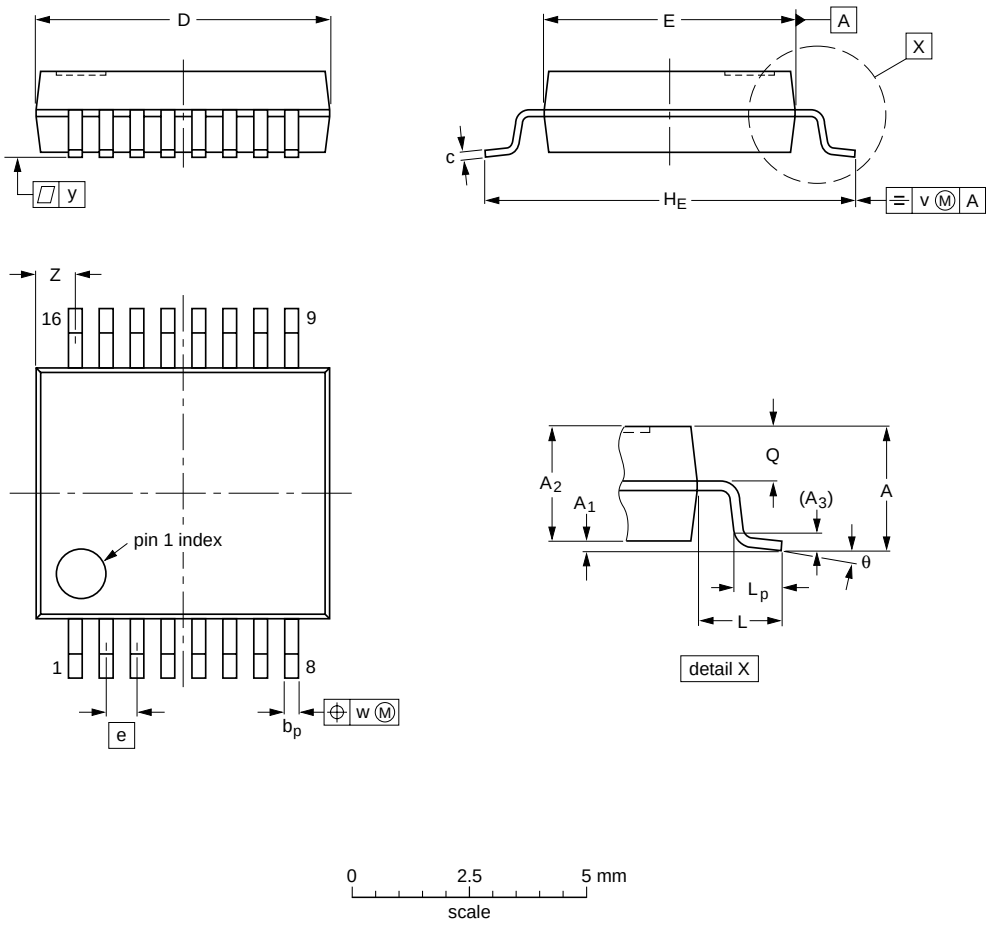
Note

1. Plastic or metal protrusions of 0.075 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT763-1	- - -	MO-241	- - -			~~02-10-17~~ 03-01-27

Fig 18. Package outline SOT763-1 (DHVQFN16)

SSOP16: plastic shrink small outline package; 16 leads; body width 5.3 mm **SOT338-1**



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	D (1)	E (1)	e	H_E	L	L_p	Q	v	w	y	Z (1)	θ
mm	2	0.21 0.05	1.80 1.65	0.25	0.38 0.25	0.20 0.09	6.4 6.0	5.4 5.2	0.65	7.9 7.6	1.25	1.03 0.63	0.9 0.7	0.2	0.13	0.1	1.00 0.55	8^o 0^o

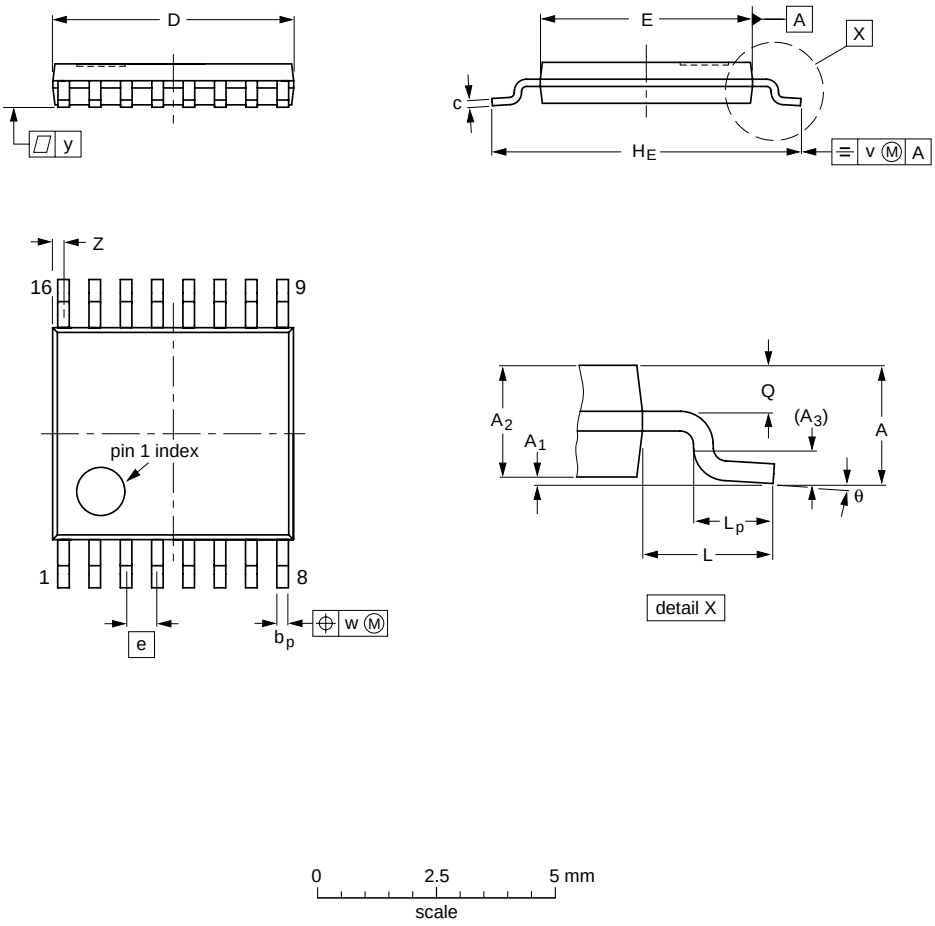
Note

1. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT338-1		MO-150				~~99-12-27~~ 03-02-19

Fig 19. Package outline SOT338-1 (SSOP16)

TSSOP16: plastic thin shrink small outline package; 16 leads; body width 4.4 mm **SOT403-1**



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	D (1)	E (2)	e	H_E	L	L_p	Q	v	w	y	Z (1)	θ
mm	1.1	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	5.1 4.9	4.5 4.3	0.65	6.6 6.2	1	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.40 0.06	8^o 0^o

Notes

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT403-1		MO-153				~~99-12-27~~ 03-02-18

Fig 20. Package outline SOT403-1 (TSSOP16)

14. Abbreviations

Table 10. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

15. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT423_3	20080724	Product data sheet	-	74HC_HCT423_CNV_2
Modifications:	• The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. • Legal texts have been adapted to the new company name where appropriate. • Section 3 “Ordering information”, Section 5 “Pinning information”and Section 13 “Package outline”, added type numbers 74HC423BQ and 74HCT423BQ (DHVQFN16 package). • Figure 4 “Logic diagram”, Figure 13 “Timing component connections” and Figure 15 “Power-down protection circuit” redrawn. • Section 10 “Dynamic characteristics” C_{PD} values added. • Figure 12 “Test circuit for measuring switching times” added. • Section 12.1 “Timing component connections” moved to Section 12. • Section 14 “Abbreviations” added.			
74HC_HCT423_CNV_2	19980708	Product specification	-	-

16. Legal information

16.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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